

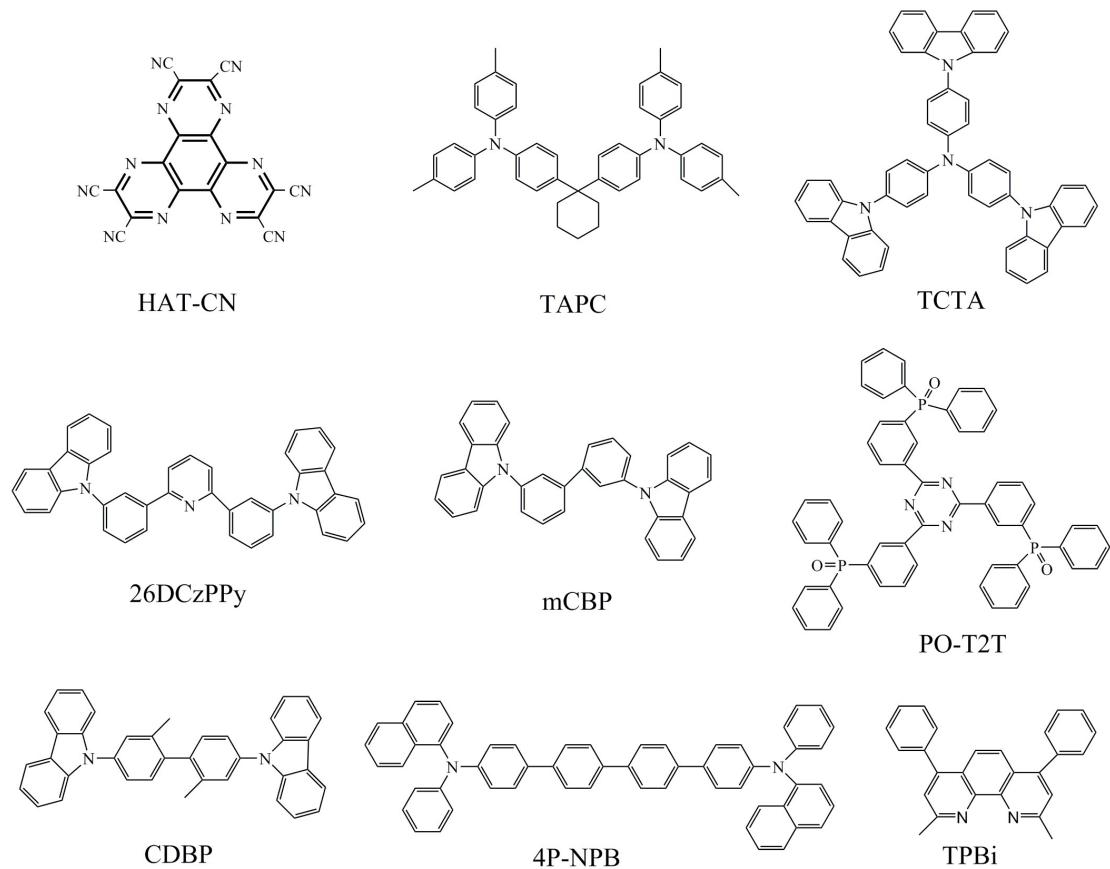
## **Electronic Supplementary Information**

### **High efficiency blue/green/yellow/red fluorescent organic light-emitting diodes sensitized by phosphors: General design rules and electroluminescence performance analysis**

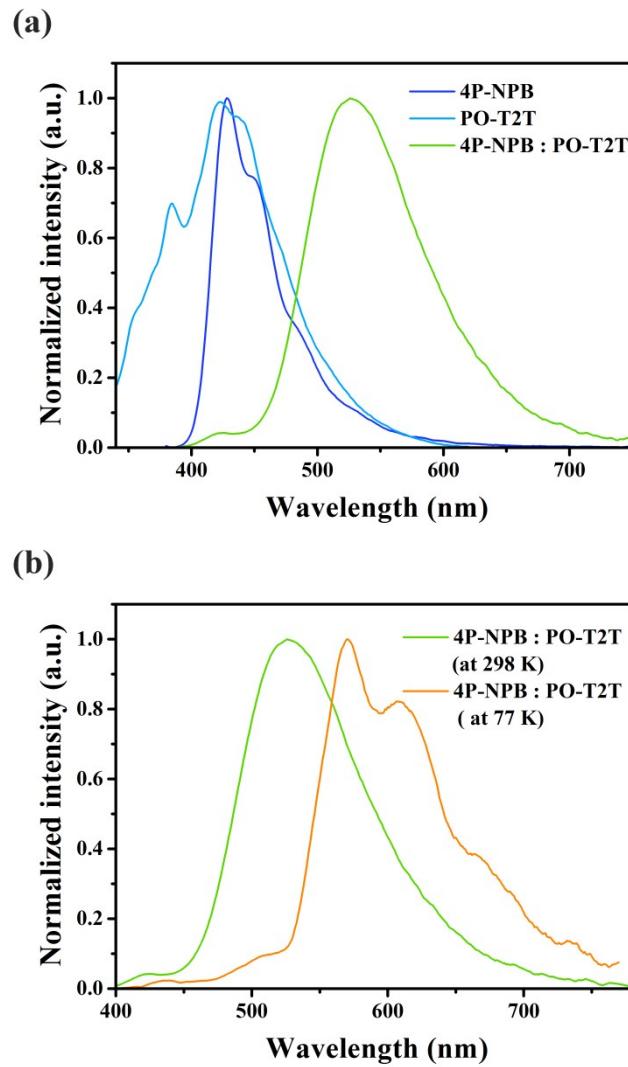
Jingwen Yao, Shian Ying, Qian Sun, Yanfeng Dai, Xianfeng Qiao, Dezhi Yang, Jiangshan Chen and Dongge Ma\*

Institute of Polymer Optoelectronic Materials and Devices, State Key Laboratory of Luminescent Materials and Devices, South China University of Technology, Guangzhou 510640, People's Republic of China

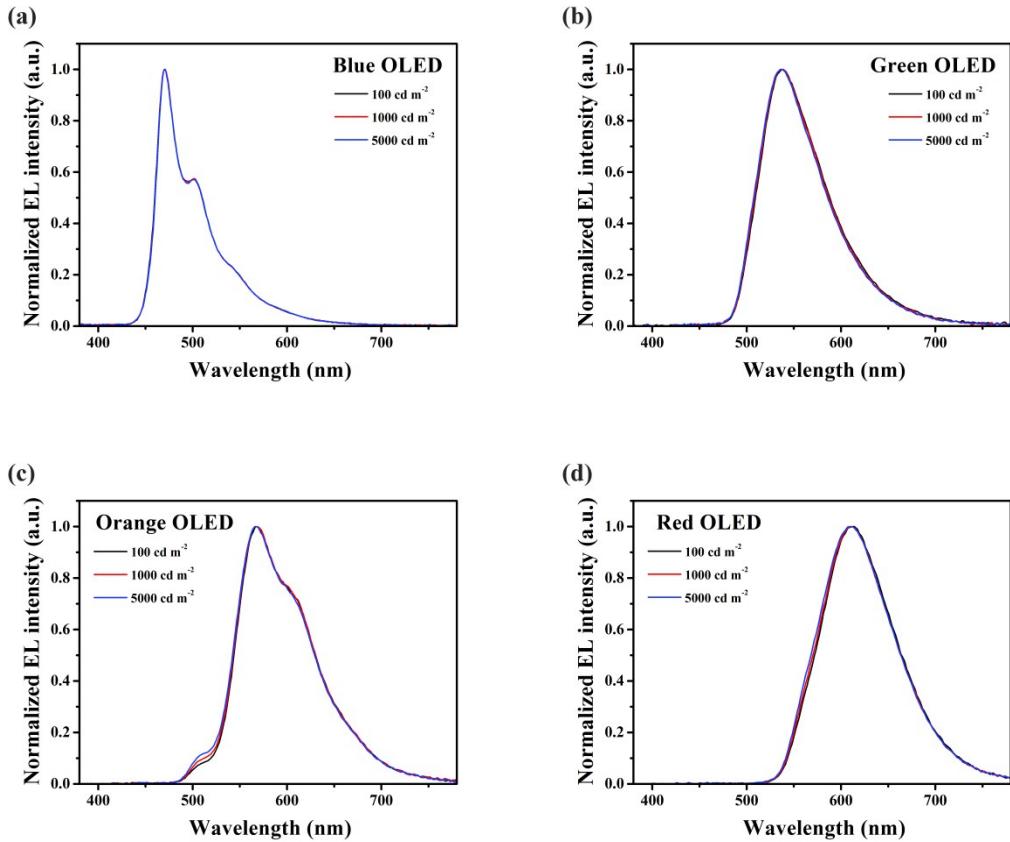
\* E-mail: [msdgma@scut.edu.cn](mailto:msdgma@scut.edu.cn)



**Fig. S1** Chemical structures of the materials used in this study.

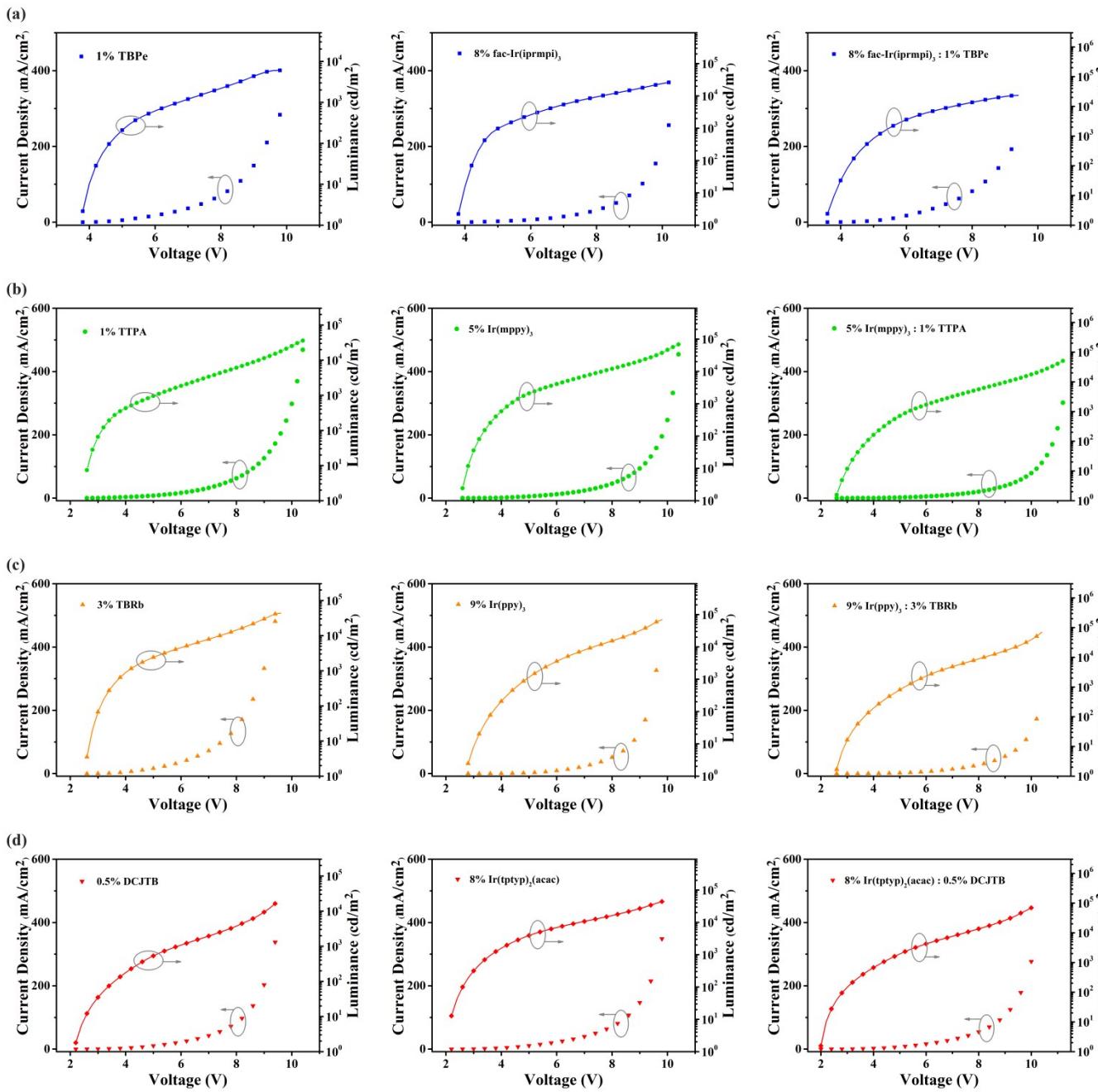


**Fig.S2** (a) PL spectra of 4P-NPB, PO-T2T and 4P-NPB:PO-T2T thin films. (b) PL spectra of 4P-NPB:PO-T2T (1:1) thin film at 298 and 77 K.

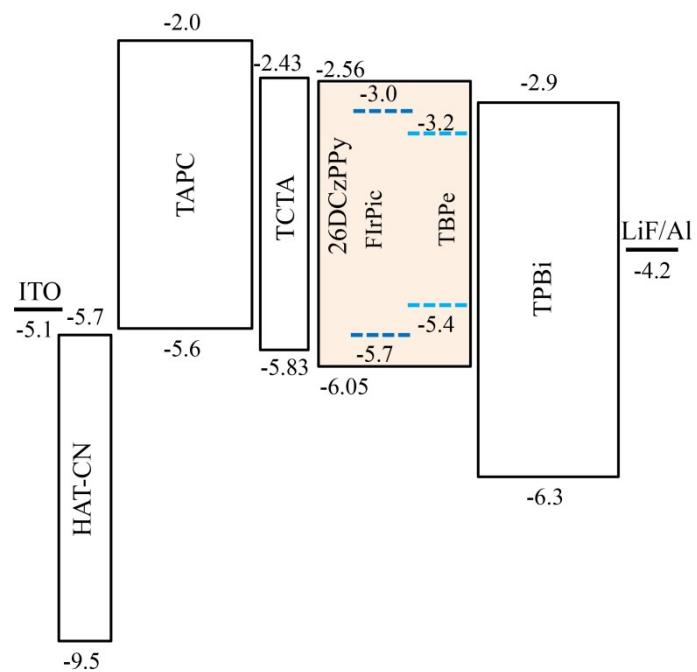


**Fig. S3** EL spectra of the resulting phosphor sensitized fluorescent OLEDs at different luminance.

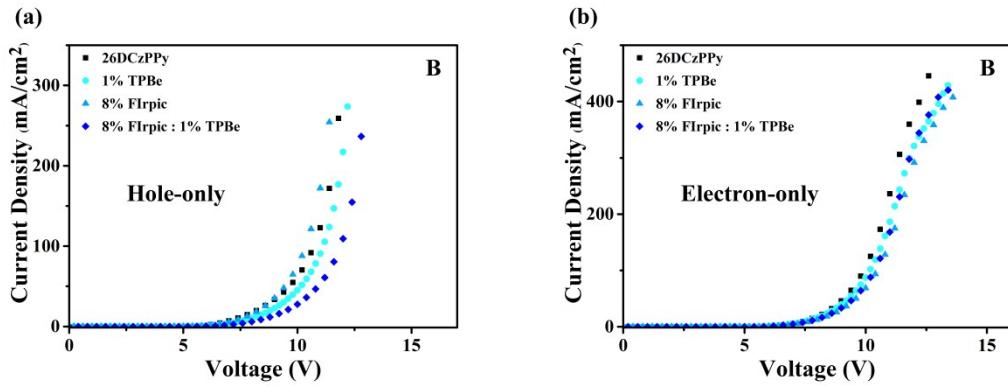
(a), (b), (c) and (d) correspond to blue, green, yellow and red fluorescent OLEDs, respectively.



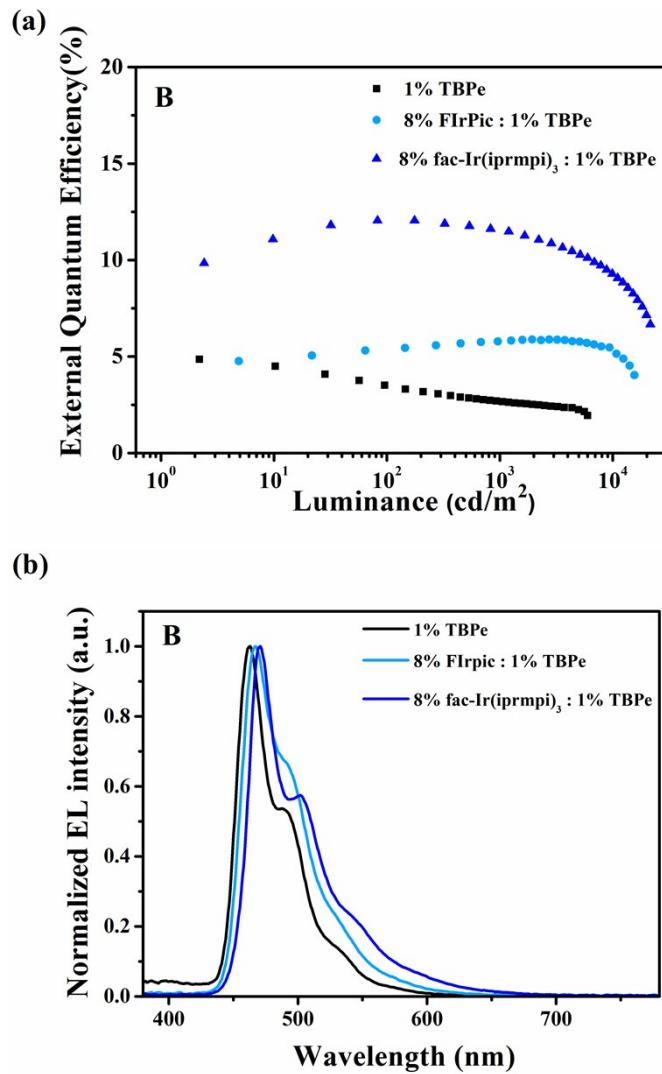
**Fig. S4** Current density-luminance-voltage (J-L-V) characteristics of the fabricated OLEDs based on only fluorescent emitters, only phosphor sensitizers and co-doped phosphor sensitizers and fluorescent emitters. (a), (b), (c) and (d) correspond to blue, green, yellow and red fluorescent OLEDs, respectively.



**Fig. S5** Schematic diagram of the phosphor sensitized blue fluorescent OLEDs based on FIrpic as sensitizer.



**Fig. S6** Current density-voltage (J-V) characteristics of the hole-only (a) and electron-only (b) devices based on Flrpic as sensitizer. The structure of the hole-only devices is: ITO/HAT-CN (15 nm)/TAPC (60 nm)/TCTA (10 nm)/EMLs (20 nm)/TCTA (10 nm)/TAPC (60 nm)/HAT-CN (15 nm)/Al. The structure of the electron-only devices is: ITO/LiF (1nm)/TPBi (45 nm)/EMLs (20 nm)/TPBi (45 nm)/LiF (1 nm)/Al. And the EMLs are 26DCzPPy, 26DCzPPy:1 wt% TBPe, 26DCzPPy:8 wt% Flrpic and 26DCzPPy:8 wt% Flrpic:1 wt% TBPe.



**Fig. S7** (a) EQE-luminance characteristics of the blue OLEDs based on TBPe, FIrpic sensitized TBPe and fac-Ir(iprmp)₃ sensitized TBPe. (b) EL spectra of the blue OLEDs based on TBPe, FIrpic sensitized TBPe and fac-Ir(iprmp)₃ sensitized TBPe at 1000 cd m⁻². The structure of the blue OLED based on FIrpic sensitized TBPe is: ITO/HAT-CN (15 nm)/TAPC (60 nm)/TCTA (10 nm)/26DCzPPy:8 wt% FIrpic:1 wt% TBPe (20 nm)/TPBi (45 nm)/LiF (1 nm)/Al.

**Table S1** EL performances of the blue OLEDs based on TBPe, FIrpic sensitized TBPe and fac-Ir(iprmpi)<sub>3</sub> sensitized TBPe.

Dopant	Voltage (V)	EQE (%)		CE (cd A <sup>-1</sup> )
		Turn-on/1000/5000 cd m <sup>-2</sup>	Max./1000/5000 cd m <sup>-2</sup>	
TBPe	3.8/6.8/9.4	4.9/2.7/2.1		6.5/3.4/2.7
<b>FIrpic+TBPe</b>	<b>4.4/6.0/7.8</b>	<b>5.9/5.8/5.8</b>		<b>9.7/9.5/9.6</b>
<b>fac-Ir(iprmpi)<sub>3</sub>+TBPe</b>	<b>3.6/5.2/6.4</b>	<b>12.1/11.5/10.3</b>		<b>23.9/22.9/20.5</b>

### Supplementary Note 1 Estimation of Förster transfer radius

Förster transfer radius ( $R_0$ ) was estimated from the overlap of PL spectrum of donor and the extinction spectrum of acceptor by using the follow equation:

$$R_0^6 = \frac{9000(\ln 10)\kappa^2\Phi_{PL}}{128\pi^5 N_A n^4} \int_0^\infty F_D(\lambda) \epsilon_A(\lambda) \lambda^4 d\lambda \quad (S1)$$

where  $\lambda$  is the wavelength,  $F_D(\lambda)$  is the spectrum distribution of donor (measured in quanta and normalized to unity on a wavelength scale),  $\epsilon_A(\lambda)$  is the molar decadic extinction coefficient of acceptor,  $\kappa^2$  is orientation factor,  $\Phi_{PL}$  is the PL quantum yield of donor,  $N_A$  is Avogadro's number,  $n$  is the refractive index of the solvent.

**Table S2** Förster transfer radii from hosts and phosphor sensitizers to fluorescent emitters in the resulting phosphor sensitized OLEDs.

EL color	Förster transfer radii <sup>a</sup> (nm)	Förster transfer radii <sup>a</sup> (nm)
Blue	6.06	3.88
Green	7.77	5.74
Yellow	6.37	6.07
Red	7.90	6.55

<sup>a</sup>) Förster transfer radii from hosts to fluorescent emitters. <sup>b</sup>) Förster transfer radiis from phosphor sensitizers to fluorescent emitters.

## **Supplementary Note 2 Structures of the single-carrier devices**

The blue hole-only devices: ITO/HAT-CN (15 nm)/TAPC (60 nm)/TCTA (10 nm)/EMLs (20 nm)/TCTA (10 nm)/TAPC (60 nm)/HAT-CN (15 nm)/Al. EMLs are 26DCzPPy, 26DCzPPy:1 wt% TBPe, 26DCzPPy:8wt% fac-Ir(iprppmi)<sub>3</sub> and 26DCzPPy:8wt% fac-Ir(iprppmi)<sub>3</sub>:1wt% TBPe.

The blue electron-only devices: ITO/LiF (1 nm)/TPBi (45 nm)/EMLs (20 nm)/TPBi (45 nm)/LiF (1 nm)/Al. EMLs are 26DCzPPy, 26DCzPPy:1 wt% TBPe, 26DCzPPy:8 wt% fac-Ir(iprppmi)<sub>3</sub> and 26DCzPPy:8 wt% fac-Ir(iprppmi)<sub>3</sub>:1 wt% TBPe.

The green hole-only devices: ITO/HAT-CN (15 nm)/TAPC (60 nm)/TCTA (5 nm)/CDBP (5 nm)/EMLs (20 nm)/CDBP (5 nm)/TCTA (5 nm)/TAPC (60 nm)/HAT-CN (15 nm)/Al. EMLs are CDBP:PO-T2T, CDBP:PO-T2T:1 wt% TTPA, CDBP:PO-T2T:5 wt% Ir(mppy)<sub>3</sub> and CDBP:PO-T2T:5 wt% Ir(mppy)<sub>3</sub>:1 wt% TTPA.

The green electron-only devices: ITO/LiF (1 nm)/PO-T2T (45 nm)/EMLs (20 nm)/PO-T2T (45 nm)/LiF (1 nm)/Al. EMLs are CDBP:PO-T2T, CDBP:PO-T2T:1 wt% TTPA, CDBP:PO-T2T:5 wt% Ir(mppy)<sub>3</sub> and CDBP:PO-T2T:5 wt% Ir(mppy)<sub>3</sub>:1 wt% TTPA.

The yellow hole-only devices: ITO/HAT-CN (15 nm)/TAPC (60 nm)/TCTA (5 nm)/mCBP (5 nm)/EMLs (20 nm)/mCBP (5 nm)/TCTA (5 nm)/TAPC (60 nm)/HAT-CN (15 nm)/Al. EMLs are mCBP:PO-T2T, mCBP:PO-T2T:3 wt% TBRb, mCBP:PO-T2T:9 wt% Ir(ppy)<sub>3</sub> and mCBP:PO-T2T:9 wt% Ir(ppy)<sub>3</sub>:3 wt% TBRb.

The yellow electron-only devices: ITO/LiF (1 nm)/PO-T2T (45 nm)/EMLs (20 nm)/PO-T2T (45 nm)/LiF (1 nm)/Al. EMLs are mCBP:PO-T2T, mCBP:PO-T2T:3 wt% TBRb, mCBP:PO-T2T:9 wt% Ir(ppy)<sub>3</sub> and mCBP:PO-T2T:9 wt% Ir(ppy)<sub>3</sub>:3 wt% TBRb.

The red hole-only devices: ITO/HAT-CN (15 nm)/TAPC (60 nm)/TCTA (5 nm)/4P-NPB (8 nm)/EMLs (20 nm)/4P-NPB (8 nm)/TCTA (5 nm)/TAPC (60 nm)/HAT-CN (15 nm)/Al. EMLs are 4P-NPB:PO-T2T, 4P-NPB:PO-T2T:0.5 wt% DCJTB, 4P-NPB:PO-T2T:8 wt% Ir(tptpy)<sub>2</sub>(acac) and 4P-NPB:PO-T2T:8 wt% Ir(tptpy)<sub>2</sub>(acac):0.5 wt% DCJTB.

The red electron-only devices: ITO/LiF (1 nm)/PO-T2T (45 nm)/EMLs (20 nm)/PO-T2T (45 nm)/LiF (1 nm)/Al. EMLs are 4P-NPB:PO-T2T, 4P-NPB:PO-T2T:0.5 wt% DCJTB, 4P-NPB:PO-T2T:8 wt% Ir(tptpy)<sub>2</sub>(acac) and 4P-NPB:PO-T2T:8 wt% Ir(tptpy)<sub>2</sub>(acac):0.5 wt% DCJTB.